

S102S11 Series S202S11 Series

*Zero cross type is also available. (\$102\$12 Series/\$202\$12 Series)

I_T(rms)≤8A, Built-in snubber circuit Non-Zero Cross type SIP 4pin Triac output SSR

■ Description

S102S11 Series and S202S11 Series Solid State Relays (SSR) are an integration of an infrared emitting diode (IRED), a Phototriac Detector and a main output Triac. These devices are ideally suited for controlling high voltage AC loads with solid state reliability while providing 4.0kV isolation ($V_{iso}(rms)$) from input to output.

■ Features

- 1. Output current, I_T(rms)≤8.0A
- 2. Non-zero crossing functionary
- 3. 4 pin SIP package
- 4. High repetitive peak off-state voltage

(V_{DRM}: 600V, S202S11 Series)

(V_{DRM}: 400V, **S102S11 Series**)

- 5. Built-in snubber circuit
- 6. High isolation voltage between input and output (V_{iso}(rms) : 4.0kV)
- 7. Lead-free terminal components are also available (see Model Line-up section in this datasheet)
- 8. Screw hole for heat sink

■ Agency approvals/Compliance

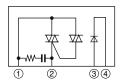
- 1. Recognized by UL508, file No. E94758 (as models No. **\$102\$11/\$202\$11**)
- Approved by CSA 22.2 No.14, file No. LR63705 (as models No. S102S11/S202S11)
- 3. Package resin: UL flammability grade (94V-0)

■ Applications

- 1. Isolated interface between high voltage AC devices and lower voltage DC control circuitry.
- 2. Switching motors, fans, heaters, solenoids, and valves.
- 3. Phase or power control in applications such as lighting and temperature control equipment.



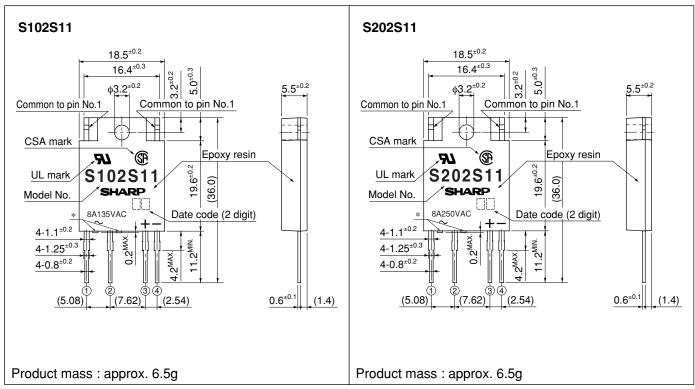
■ Internal Connection Diagram



- ① Output (Triac T2)
- ② Output (Triac T1)
- ③ Input (+)
- 4 Input (-)

■ Outline Dimensions

(Unit: mm)



- *: Do not allow external connection.
- (): Typical dimensions



Date code (2 digit)

1st digit				2nd digit		
Year of production				Month of production		
A.D.	Mark	A.D	Mark	Month	Mark	
1990	A	2002	P	January	1	
1991	В	2003	R	February	2	
1992	С	2004	S	March	3	
1993	D	2005	T	April	4	
1994	Е	2006	U	May	5	
1995	F	2007	V	June	6	
1996	Н	2008	W	July	7	
1997	J	2009	X	August	8	
1998	K	2010	A	September	9	
1999	L	2011	В	October	0	
2000	M	2012	С	November	N	
2001	N	:	:	December	D	

repeats in a 20 year cycle

Country of origin Japan

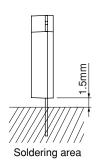
Rank mark

There is no rank mark indicator and currently there are no rank offered for this device.



■ Absolute Maximum Ratings

■ Absolute Maximum Ratings $(T_a=25^{\circ}C)$							
	Parameter	Symbol	Rating	Unit			
Ŧ .	Forward current	I_F	50 *3	mA			
Input	Reverse voltage	V_R	6	V			
	RMS ON-state current	I _T (rms)	8 *3	A			
	Peak one cycle surge of	I _{surge}	80 *4	A			
	Repetitive	S102S11		400	3.7		
	peak OFF-state voltage	S202S11	VDRM	600	V		
Output	Non-Repetitive	S102S11	* 7	400	* 7		
	peak OFF-state voltage	S202S11	VDSM	600	V		
	Critical rate of rise of ON	dI _T /dt	50	A/μs			
	Operating frequency	f	45 to 65	Hz			
*1 Isolatic	on voltage	V _{iso} (rms)	4.0	kV			
Operating temperature			Topr	-20 to +80	°C		
Storage	e temperature	T_{stg}	-30 to +100	°C			
*2Soldering temperature			T _{sol}	260	°C		



■ Electro-optical Characteristics

 $(T_a=25^{\circ}C)$

Parameter			Symbol	Conditions	MIN.	TYP.	MAX.	Unit	
T4	Forward voltage		V_F	I _F =20mA	_	1.2	1.4	V	
Input	Reverse current		I_R	V _R =3V	_	_	100	μΑ	
-	ON-state voltage		V _T (rms)	I _T (rms)=2A, Resistance load, I _F =20mA	-	_	1.5	V	
	Minimum Operating current	S102S11	I (mms)	V _{OUT} (rms)=120V	50				
		S202S11	I _{OP} (rms)	V _{OUT} (rms)=240V	_	_	50	mA	
Output	Oman singuit leals symment	S102S11	I (********)	V _{OUT} (rms)=120V	-	_	5	4	
	Open circuit leak current	S202S11	I _{leak} (rms)	V _{OUT} (rms)=240V	_	_	10	mA	
	Critical rate of rise of OFF-state voltage		dV/dt	V _D =2/3•V _{DRM}	30	_	_	V/µs	
	Critical rate of rise of OFF-state voltage at commutaion		(dV/dt)c	$T_j=125^{\circ}C, V_D=2/3 \bullet V_{DRM}, dI_T/dt=-4.0A/ms$	5	_	-	V/µs	
	Minimum trigger current		I_{FT}	$V_D=12V, R_L=30\Omega$	_	_	8	mA	
	Isolation resistance		R _{ISO}	DC500V, 40 to 60%RH	10^{10}	_	_	Ω	
	Turn-on time	S102S11	$V_D(rms)=100V$, AC60Hz			1			
				I _T (rms)=2A, Resistance load, I _F =20mA	_	_	1	me	
Transfer charac-		S202S11	$V_D(rms)=200V$, AC60Hz			1	ms		
teristics		3202311		I _T (rms)=2A, Resistance load, I _F =20mA	_	_	1		
		S102S11	$V_D(rms)=100V$, AC60Hz			0.2			
	Tum off time			I _T (rms)=2A, Resistance load, I _F =20mA	_	_	9.3	ms	
	Turn-off time	S202S11	2 S11 t _{off}	V _D (rms)=200V, AC60Hz		-	9.3		
		3202311		I _T (rms)=2A, Resistance load, I _F =20mA	_				
Thermal resistance		R _{th} (j-c)	Between junction and case –		4.0	_	°C/W		
		R _{th} (j-a)	Between junction and ambient	-	40	_	C/ W		

^{*1 40} to 60%RH, AC for 1minute, f=60Hz *2 For 10s

^{*3} Refer to Fig.1, Fig.2 *4 f=50Hz sine wave, T_j=25°C start



■ Model Line-up (1) (Lead-free terminal components)

Shinning Doolsogo	Case	$ m V_{DRM}$	I _{FT} [mA]		
Shipping Package	200pcs/case	[V]	$(V_D=12V, R_L=30\Omega)$		
Model No.	S102S11F	400	MAX.8		
Model No.	S202S11F	600	MAX.8		

■ Model Line-up (2) (Lead solder plating components)

Shipping Package	Case 200pcs/case	V _{DRM} [V]	$I_{FT}[mA] \\ (V_D=12V, \\ R_L=30\Omega)$	
Model No	S102S11	400	MAX.8	
Model No.	S202S11	600	MAX.8	

Please contact a local SHARP sales representative to see the actual status of the production.



Fig.1 Forward Current vs. Ambient Temperature

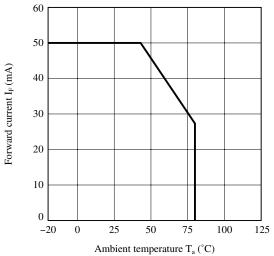


Fig.3 RMS ON-state Current vs. Case Temperature

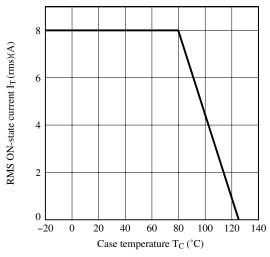


Fig.5 Surge Current vs. Power-on Cycle

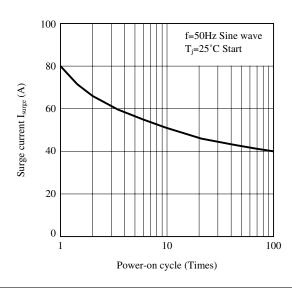


Fig.2 RMS ON-state Current vs.
Ambient Temperature

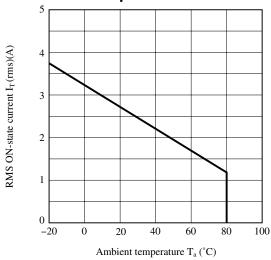


Fig.4 Forward Current vs. Forward Voltage

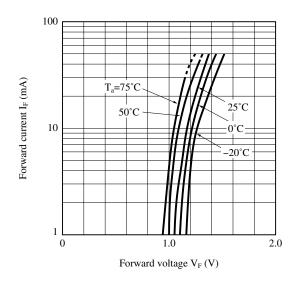


Fig.6 Maximum ON-state Power Dissipation vs. RMS ON-state Current

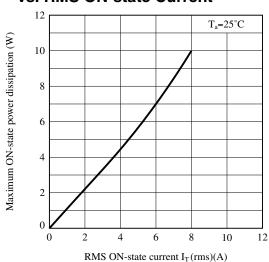




Fig.7 Minimum Trigger Current vs.
Ambient Temperature

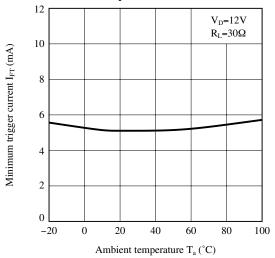
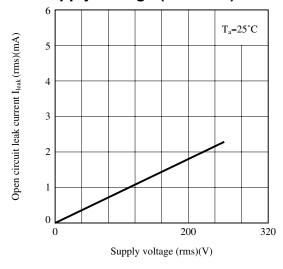
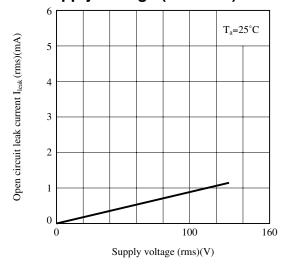


Fig.8-b Open Circuit Leak Current vs. Supply Voltage (S202S11)



Remarks: Please be aware that all data in the graph are just for reference.

Fig.8-a Open Circuit Leak Current vs. Supply Voltage (S102S11)





■ Design Considerations

Recommended Operating Conditions

Parameter			Symbol	Conditions	MIN.	MAX.	Unit
Input signal current at ON state		I _F (ON)	_	16	24	mA	
Input	Input signal current at OFF state		I _F (OFF)	_	0	0.1	mA
Output	Load supply voltage	S102S11	V _{OUT} (rms)	-	80	120	V
		S202S11			80	240	
	Load supply current		I _{OUT} (rms)	_	0.1	I _T (rms)×80%(*)	mA
	Frequency		f	_	47	63	Hz
Operating temperature		T_{opr}	_	-20	80	°C	

^(*) See Fig.2 about derating curve (I_T(rms) vs. ambient temperature).

Design guide

In order for the SSR to turn off, the triggering current (I_F) must be 0.1mA or less.

In phase control applications or where the SSR is being by a pulse signal, please ensure that the pulse width is a minimum of 1ms.

For over voltage protection, a Varistor may be used.

A varistor used for the above mentioned scenarios should be located as close to the main output triac as possible.

The load current should be within the bounds of derating curve. (Refer to Fig.2) Also, please use the optional heat sink when necessary.

In case the optional heat sink is used and the isolation voltage between the device and the optional heat sink is needed, please locate the insulation sheet between the device and the heat sink.

When the optional heat sink is equipped, please set up the M3 screw-fastening torque at 0.3 to 0.5N• m. In order to dissipate the heat generated from the inside of device effectively, please follow the below suggestions.

- (a) Make sure there are no warps or bumps on the heat sink, insulation sheet and device surface.
- (b) Make sure there are no metal dusts or burrs attached onto the heat sink, insulation sheet and device surface.
- (c) Make sure silicone grease is evenly spread out on the heat sink, insulation sheet and device surface.

Silicone grease to be used is as follows;

- 1) There is no aged deterioration within the operating temperature ranges.
- 2) Base oil of grease is hardly separated and is hardly permeated in the device.
- 3) Even if base oil is separated and permeated in the device, it should not degrade the function of a device.

Recommended grease: G-746 (Shin-Etsu Chemical Co., Ltd.)

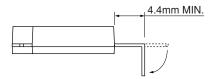
: G-747 (Shin-Etsu Chemical Co., Ltd.)

: SC102 (Dow Corning Toray Silicone Co., Ltd.)

In case the optional heat sink is screwed up, please solder after screwed.



In case of the lead frame bending, please keep the following minimum distance and avoid any mechanical stress between the base of terminals and the molding resin.



Some of AC electromagnetic counters or solenoids have built-in rectifier such as the diode.

In this case, please use the device carefully since the load current waveform becomes similar with rectangular waveform and this results may not make a device turn off.

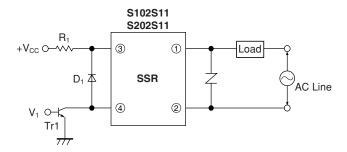
Degradation

In general, the emission of the IRED used in SSR will degrade over time.

In the case where long term operation and / or constant extreme temperature fluctuations will be applied to the devices, please allow for a worst case scenario of 50% degradation over 5years.

Therefore in order to maintain proper operation, a design implementing these SSRs should provide at least twice the minimum required triggering current from initial operation.

Standard Circuit



[☆] For additional design assistance, please review our corresponding Optoelectronic Application Notes.



■ Manufacturing Guidelines

Soldering Method

Flow Soldering (No solder bathing)

Flow soldering should be completed below 260°C and within 10s.

Preheating is within the bounds of 100 to 150°C and 30 to 80s.

Please solder within one time.

Other notices

Please test the soldering method in actual condition and make sure the soldering works fine, since the impact on the junction between the device and PCB varies depending on the tooling and soldering conditions.



Cleaning instructions

Solvent cleaning:

Solvent temperature should be 45°C or below. Immersion time should be 3minutes or less.

Ultrasonic cleaning:

The impact on the device varies depending on the size of the cleaning bath, ultrasonic output, cleaning time, size of PCB and mounting method of the device.

Therefore, please make sure the device withstands the ultrasonic cleaning in actual conditions in advance of mass production.

Recommended solvent materials:

Ethyl alcohol, Methyl alcohol and Isopropyl alcohol.

In case the other type of solvent materials are intended to be used, please make sure they work fine in actual using conditions since some materials may erode the packaging resin.

Presence of ODC

This product shall not contain the following materials.

And they are not used in the production process for this device.

Regulation substances: CFCs, Halon, Carbon tetrachloride, 1.1.1-Trichloroethane (Methylchloroform)

Specific brominated flame retardants such as the PBBOs and PBBs are not used in this product at all.



■ Package specification

Package materials

Packing case: Corrugated cardboard
Partition: Corrugated cardboard
Pad: Corrugated cardboard
Cushioning material: Polyethylene

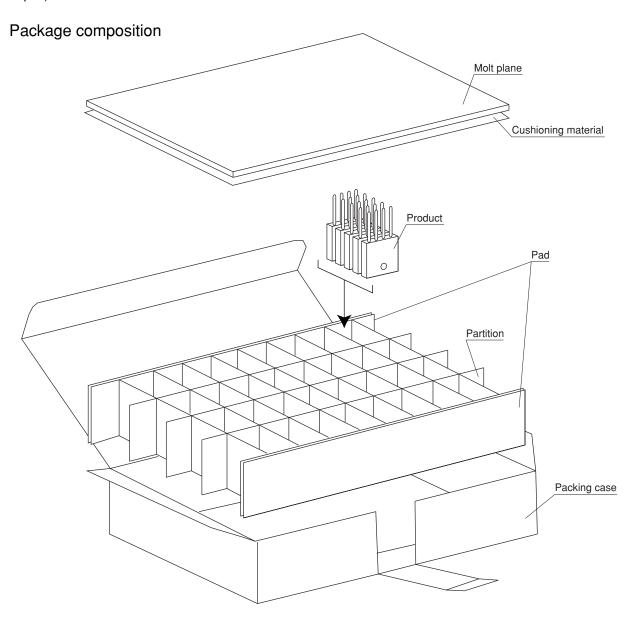
Molt plane: Urethane

Package method

The product should be located after the packing case is partitioned and protected inside by 4 pads.

Each partition should have 5 products with the lead upward.

Cushioning material and molt plane should be located after all products are settled (1 packing contains 200 pcs).





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- --- Various safety devices, etc.
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